

AMENDMENTS TO THE CLAIMS:

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A process for producing an electronic device material[[,]] comprising[[(:]] forming a film on the surface of an electronic device substrate by using a plasma based on microwave irradiation via a plane antenna member having a plurality of slits, in the presence of a process gas comprising at least a gas containing a film-forming substance and a rare gas.

2. (original) A process for producing an electronic device material according to claim 1, wherein the electronic device substrate is a semiconductor device substrate.

3. (currently amended) A process for producing an electronic device material according to ~~claim 1 or 2~~ claim 2, wherein the electronic device substrate ~~mainly~~ comprises Si.

4. (currently amended) A process for producing an electronic device material according to ~~any one of claims 1 to 3~~ claim 3, wherein the film formation provides an insulating film formed on the substrate.

5. (original) A process for producing an electronic device material according to claim 4, wherein the film-forming substance is a film-forming substance for gate insulator of a field-effect transistor.

6. (currently amended) A process for producing an electronic device material according to ~~claim 4 or 5~~ claim 5, wherein the filmforming substance for gate insulator comprises at least one substance selected from the group consisting of: SiO₂, Si₃N₄, Ta₂O₅, ZrO₂, HfO₂, Al₂O₃, La₂O₃, TiO₂, Y₂O₃, BST (~~barium strontium titanate (Ba, Sr) TiO₃~~), Pr₂O₃, Gd₂O₃, CeO₂ and compounds of these substances.

7. (currently amended) A process for producing an electronic device material according to ~~any one of claims 1 to 6~~ claim 6, wherein the process gas further contains an organic source (~~organometallic compound~~).

8. (currently amended) A process for producing an electronic device material according to ~~any one of claims 4 to 7~~ claim 6, wherein the carbon concentration in the insulating film is 15% or less.

9. (original) A process for producing an electronic device material according to claim 4, wherein the film-forming substance is a film-forming substance for an interlayer insulating film.

10. (currently amended) A process for producing an electronic device material according to claim 9, wherein the film-forming substance for the interlayer insulating film contains at least one ~~or more~~ atom selected from the group consisting of Si, C, O, F, N and H.

11. (currently amended) A process for producing an electronic device material according to ~~any one of claims 1 to 10~~ claim 4, wherein the plasma has an electron temperature of 2 eV or less and an electron density of $1 \times 10^{11}/\text{cm}^3$ or more.

12. (currently amended) A process for producing an electronic device material according to ~~any one of claims 1 to 11~~ claim 4, wherein the electronic device is a semiconductor device.